



ACTT2S-800ETN

Enhanced, high temperature ACTT power switch

Rev - 01 24 July 2017

Product data sheet

1. General description

Planar passivated AC Thyristor Triac power switch in a TO252 (DPAK) surface mountable plastic package with self-protective capabilities against low and high energy transients. This "series ETN" triac will commute the full RMS current at the maximum rated junction temperature ($T_{j(max)} = 150\text{ °C}$) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)
- High minimum IGT for guaranteed immunity to gate noise
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Less sensitive gate for high noise immunity
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt and IEC 61000-4-4 fast transient
- Package meets UL94V0 flammability requirement
- Package is RoHS compliant

3. Applications

- AC pumps and fans
- High power solenoids
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Applications subject to high temperature ($T_{j(max)} = 150\text{ °C}$)

4. Quick reference data

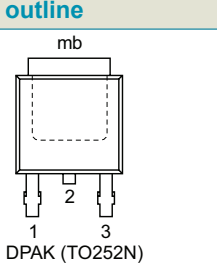

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
Absolute maximum rating				
V_{DRM}	repetitive peak off-state voltage		800	V
$I_{T(RMS)}$	RMS on-state current	square-wave pulse; $T_{mb} \leq 140\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	2	A
I_{TSM}	non-repetitive peak forward current	full sine wave; $t_p = 20\text{ ms}$; $T_{j(init)} = 25\text{ °C}$; Fig. 4 ; Fig. 5	18	A
		full sine wave; $t_p = 16.7\text{ ms}$; $T_{j(init)} = 25\text{ °C}$	19.8	A
T_j	junction temperature		150	°C

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+ T _j = 25 °C; Fig. 7	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G- T _j = 25 °C; Fig. 7	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G- T _j = 25 °C; Fig. 7	-	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 9	-	-	10	mA
V _T	on-state voltage	I _T = 3 A; T _j = 25 °C; Fig. 10	-	-	2	V
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	500	-	-	V/μs
		V _{DM} = 536 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	200	-	-	V/μs
dI _{com} /dt	rate of change of commutating current	V _D = 400 V; T _j = 150 °C; I _{T(RMS)} = 2 A; dV _{com} /dt = 20 V/μs; gate open circuit; snubberless condition	1	-	-	A/ms
		V _D = 400 V; T _j = 150 °C; I _{T(RMS)} = 2 A; dV _{com} /dt = 10 V/μs; gate open circuit	1.5	-	-	A/ms
		V _D = 400 V; T _j = 150 °C; I _{T(RMS)} = 2 A; dV _{com} /dt = 1 V/μs; gate open circuit	3	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>DPAK (TO252N)</p>	 <p>sym051</p>
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
ACTT2S-800ETN	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	TO252N

7. Marking

Table 4. Marking codes

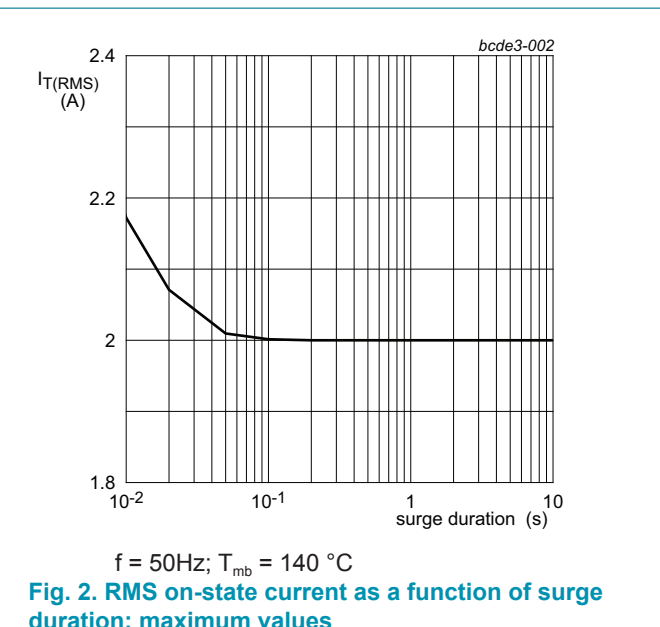
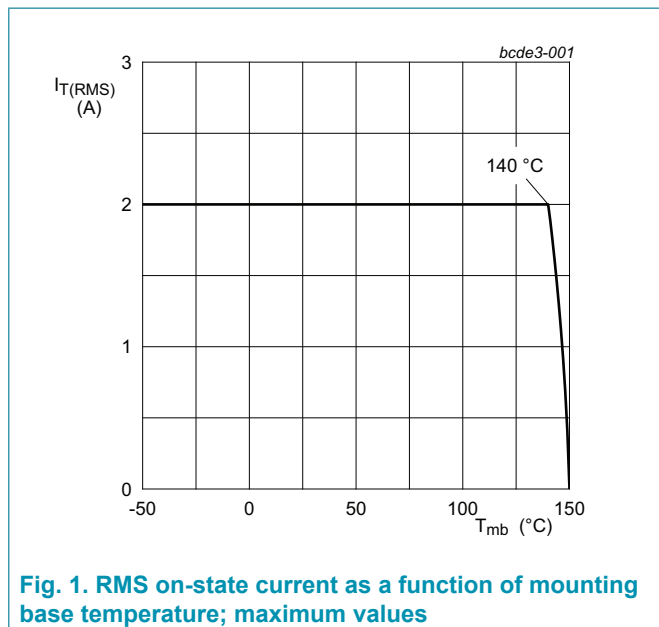
Type number	Marking codes
ACTT2S-800ETN	ACTT2S-800ETN

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 140^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	2	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $t_p = 20\text{ ms}$; $T_{j(\text{init})} = 25^{\circ}\text{C}$; Fig. 4 ; Fig. 5	18	A
		full sine wave; $t_p = 16.7\text{ ms}$; $T_{j(\text{init})} = 25^{\circ}\text{C}$	19.8	A
I^2t	I^2t for fusing	$t_p = 10\text{ms}$; sine wave	1.62	A^2/s
dI_T/dt	rate of rise of on-state current	$I_G = 70\text{mA}$	100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		2	A
P_{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T_{stg}	storage temperature		-40 to 150	$^{\circ}\text{C}$
T_j	junction temperature		150	$^{\circ}\text{C}$
V_{pp}	peak pulse voltage	$T_j = 25^{\circ}\text{C}$; non-repetitive, off-state; ten pulses on each voltage polarity; 20s or more between successive pulses	2	kV



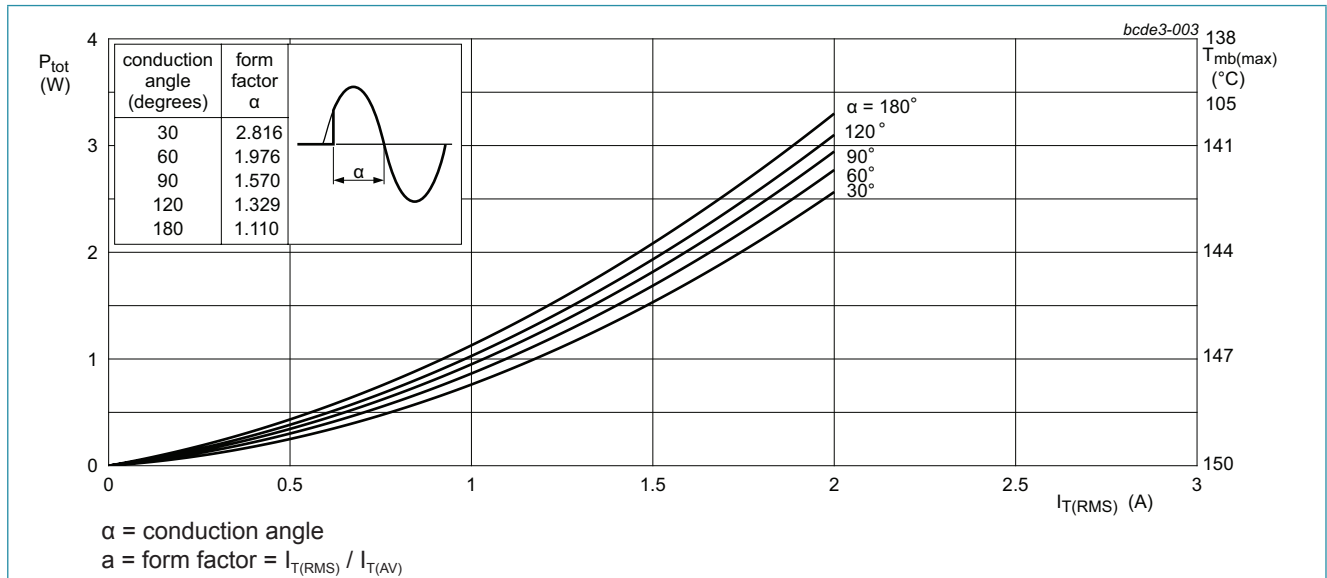


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

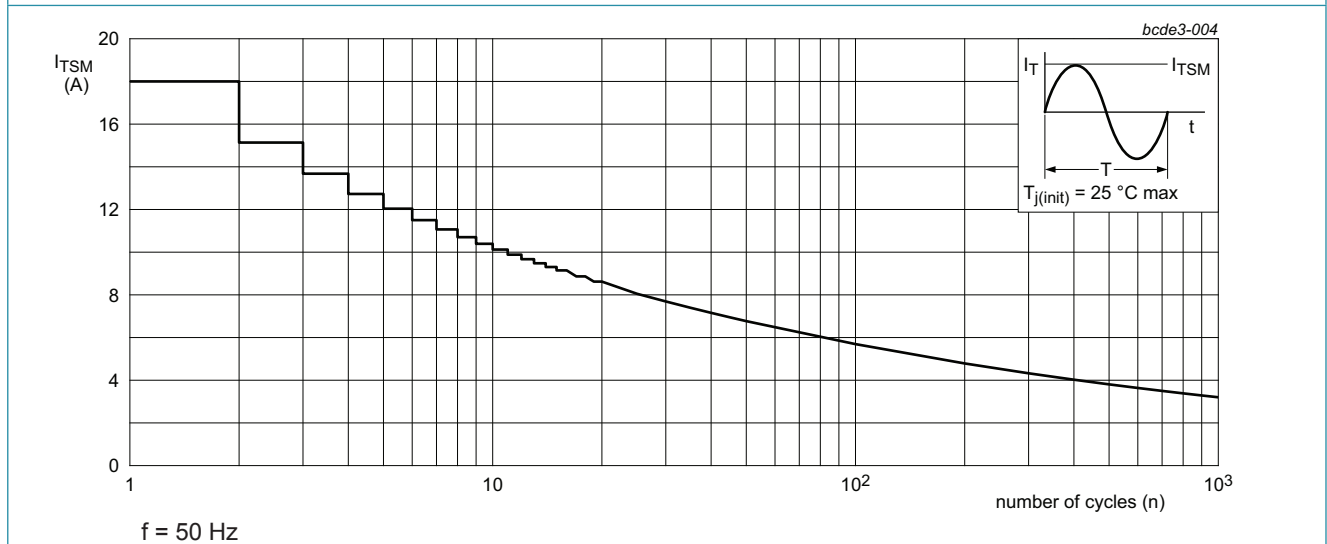


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

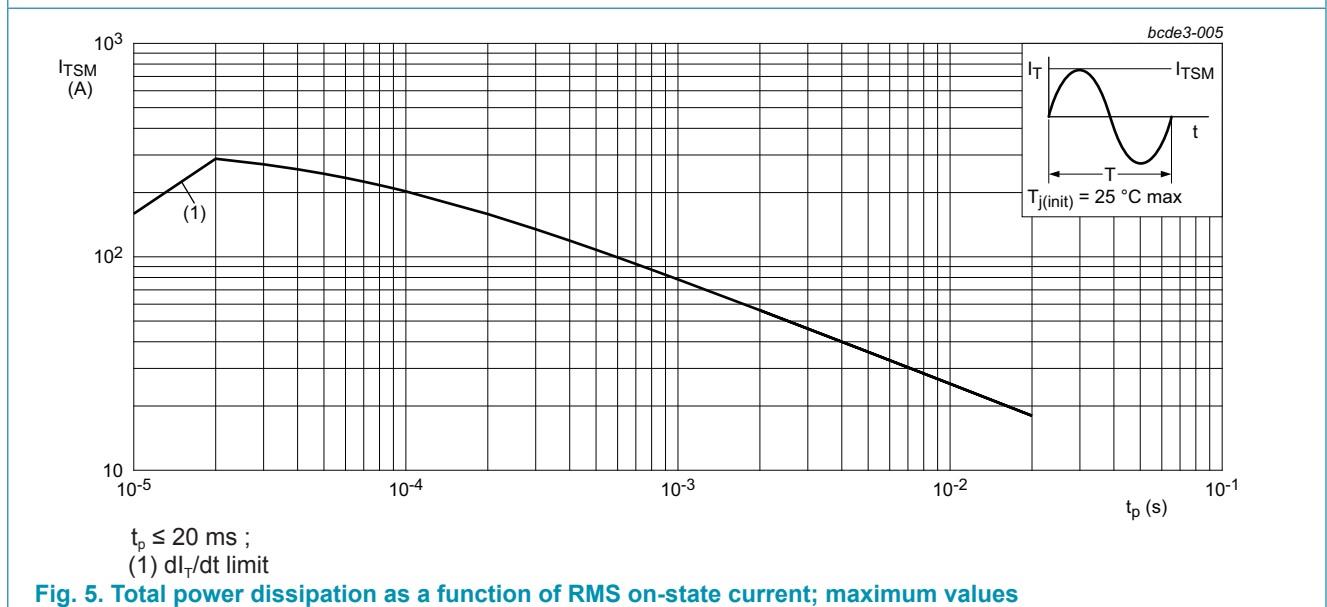


Fig. 5. Total power dissipation as a function of RMS on-state current; maximum values

9. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6	-	-	3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	75	-	K/W

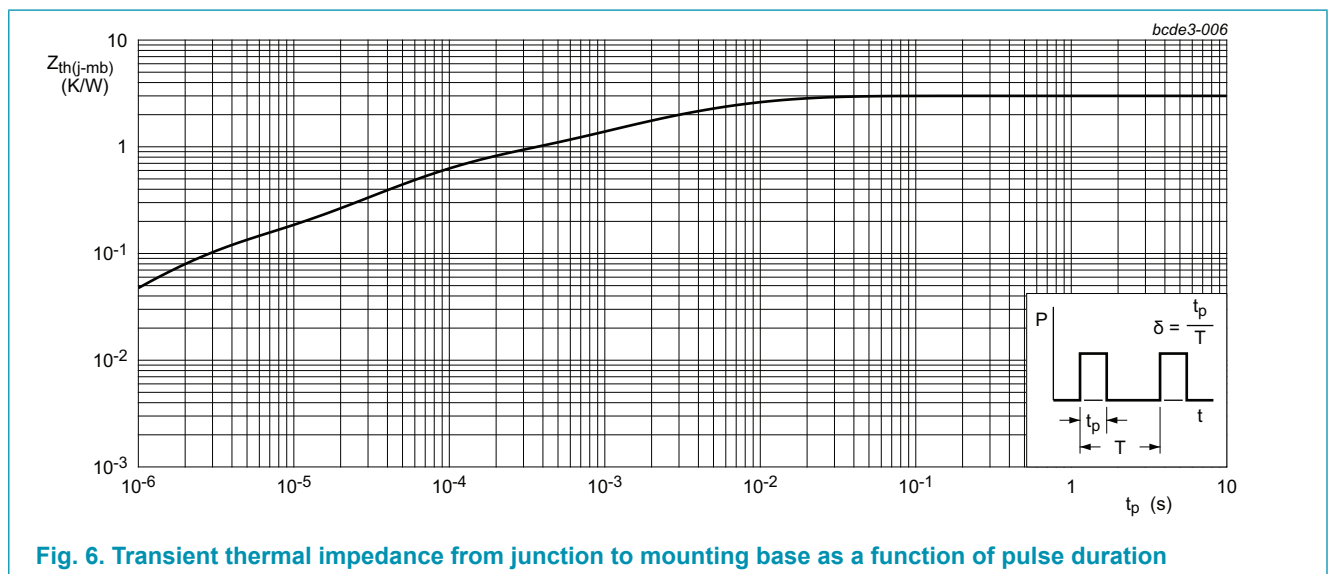
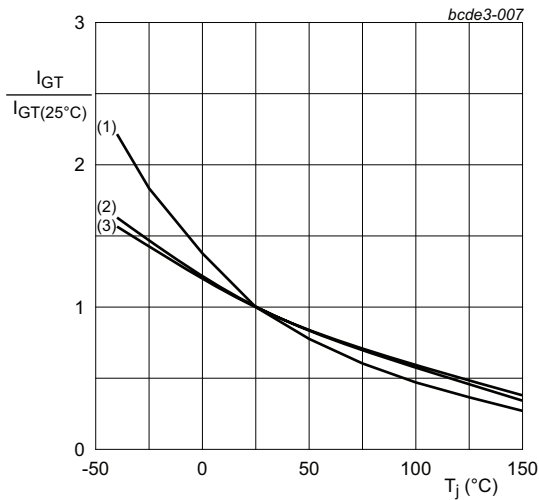


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ °C}$; Fig. 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ °C}$; Fig. 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ °C}$; Fig. 7	-	-	10	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ °C}$; Fig. 8	-	-	25	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ °C}$; Fig. 8	-	-	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ °C}$; Fig. 8	-	-	25	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ °C}$; Fig. 9	-	-	10	mA
V_T	on-state voltage	$I_T = 3\text{ A}$; $T_J = 25\text{ °C}$; Fig. 10	-	-	2	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ °C}$; Fig. 11	-	0.8	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 150\text{ °C}$; Fig. 11	0.2	0.45	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_J = 25\text{ °C}$	-	-	10	μA
		$V_D = 800\text{ V}$; $T_J = 150\text{ °C}$	-	-	2	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_J = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	500	-	-	V/ μs
		$V_{DM} = 536\text{ V}$; $T_J = 150\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	200	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_J = 150\text{ °C}$; $I_{T(RMS)} = 2\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; gate open circuit; snubberless condition	1	-	-	A/ms
		$V_D = 400\text{ V}$; $T_J = 150\text{ °C}$; $I_{T(RMS)} = 2\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit	1.5	-	-	A/ms
		$V_D = 400\text{ V}$; $T_J = 150\text{ °C}$; $I_{T(RMS)} = 2\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit	3	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

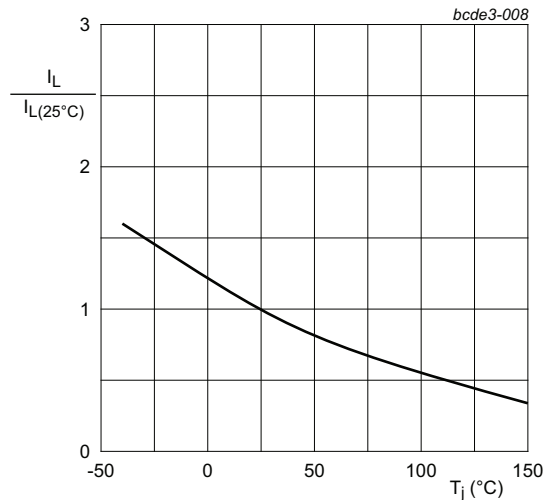


Fig. 8. Normalized latching current as a function of junction temperature

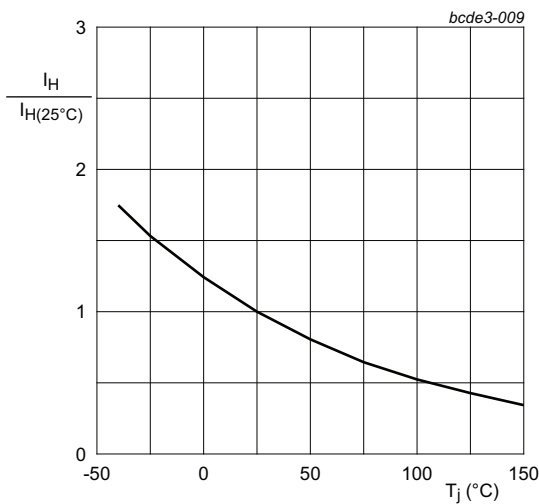
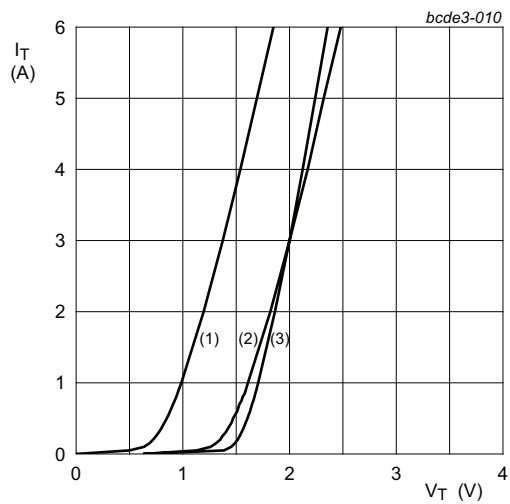


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 0.673 \text{ V}$; $R_s = 0.5217 \Omega$

- (1) $T_j = 150^\circ\text{C}$; typical values
- (2) $T_j = 150^\circ\text{C}$; maximum values
- (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

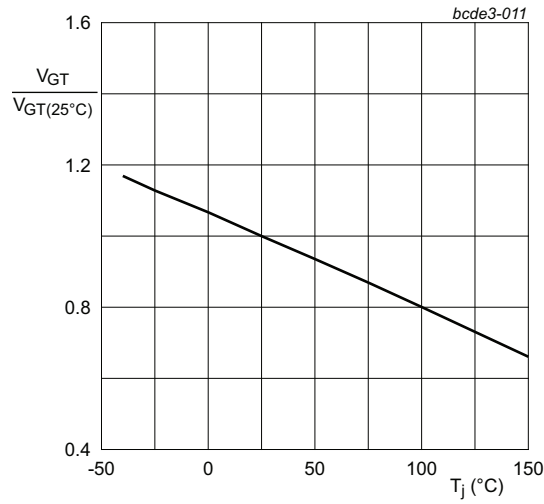
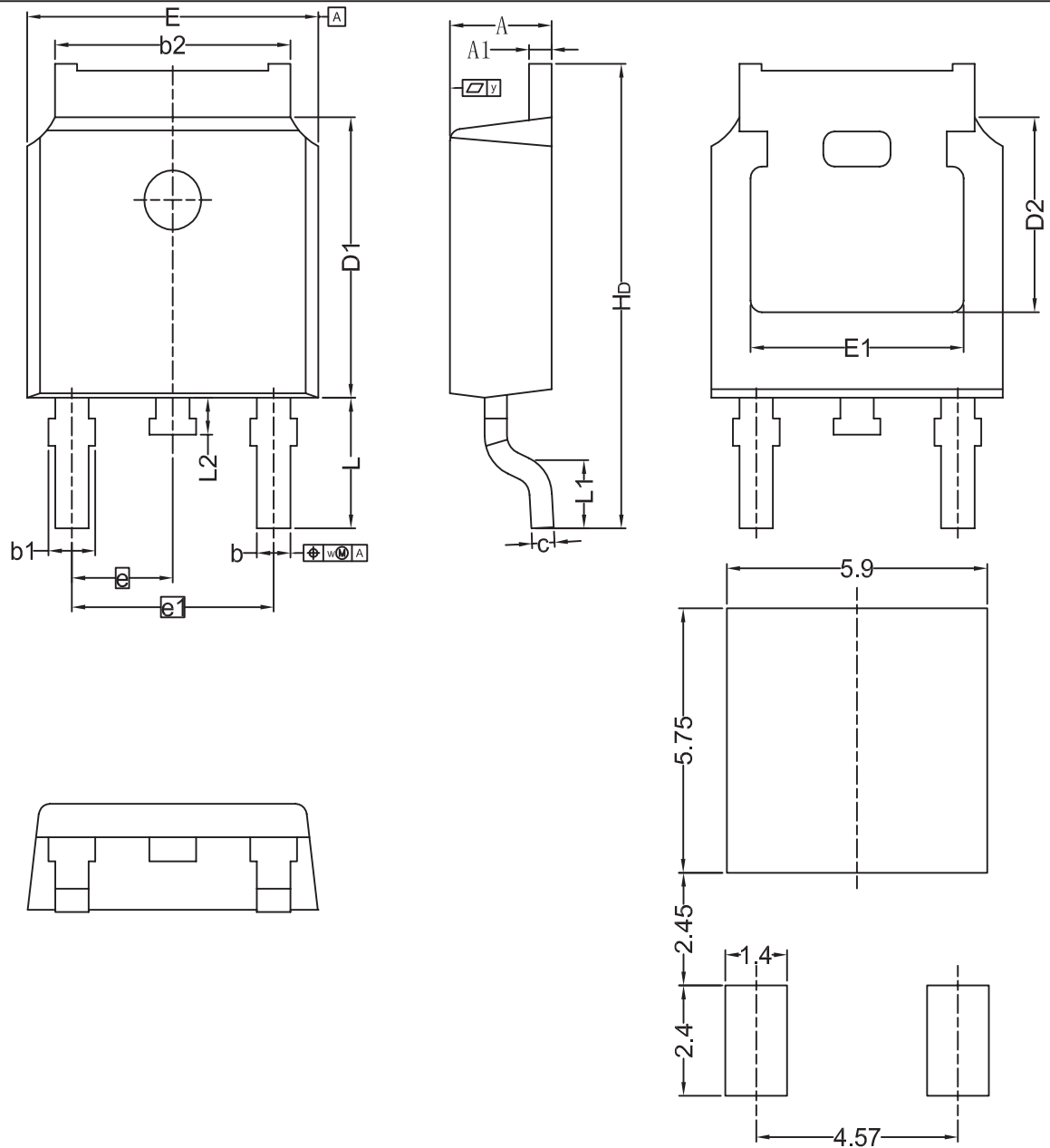


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

TO252



Recommended Footprint

Unit	A	A1	b	b1	b2	c	D1	D2	E	E1	e	e1	H _p	L	L1	L2	w	y
min	2.22	0.46	0.71	0.72	5.00	0.20	5.98	4.00	6.47	4.45	2.285	4.57	9.60	2.90 (Ref.)	0.50	0.50	0.20	
nom																		
max	2.38	0.93	0.89	1.10	5.46	0.56	6.22	---	6.73	---			10.40		---	0.90		0.20

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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